

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

350A



case style TO-200AB (A-PUK)

Major Ratings and Characteristics

| Parameters | ST180C..C | Units |
|-------------------|----------------|-------------------|
| $I_{T(AV)}$ | 350 | A |
| @ T_{hs} | 55 | °C |
| $I_{T(RMS)}$ | 660 | A |
| @ T_{hs} | 25 | °C |
| I_{TSM} | @ 50Hz 5000 | A |
| | @ 60Hz 5230 | A |
| I^2t | @ 50Hz 125 | KA ² s |
| | @ 60Hz 114 | KA ² s |
| V_{DRM}/V_{RRM} | 400 to 2000 | V |
| t_q typical | 100 | μs |
| T_J | - 40 to 125 | °C |

ELECTRICAL SPECIFICATIONS

Voltage Ratings

| Type number | Voltage Code | V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V | V_{RSM} , maximum non-repetitive peak voltage V | I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA |
|-------------|--------------|---|--|---|
| ST180C..C | 04 | 400 | 500 | 30 |
| | 08 | 800 | 900 | |
| | 12 | 1200 | 1300 | |
| | 16 | 1600 | 1700 | |
| | 18 | 1800 | 1900 | |
| | 20 | 2000 | 2100 | |

On-state Conduction

| Parameter | ST180C..C | Units | Conditions | |
|--|------------|--------------------|--|----------------|
| $I_{T(AV)}$ Max. average on-state current @ Heatsink temperature | 350 (140) | A | 180° conduction, half sine wave double side (single side) cooled | |
| | 55 (85) | °C | | |
| $I_{T(RMS)}$ Max. RMS on-state current | 660 | A | @ 25°C heatsink temperature double side cooled | |
| I_{TSM} Max. peak, one-cycle non-repetitive surge current | 5000 | | t = 10ms | No voltage |
| | 5230 | | t = 8.3ms | reapplied |
| | 4200 | | t = 10ms | 100% V_{RRM} |
| | 4400 | | t = 8.3ms | reapplied |
| I^2t Maximum I^2t for fusing | 125 | KA ² s | t = 10ms | No voltage |
| | 114 | | t = 8.3ms | reapplied |
| | 88 | | t = 10ms | 100% V_{RRM} |
| | 81 | | t = 8.3ms | reapplied |
| $I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing | 1250 | KA ² /s | t = 0.1 to 10ms, no voltage reapplied | |
| $V_{T(TO)1}$ Low level value of threshold voltage | 1.08 | V | (16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ max. | |
| $V_{T(TO)2}$ High level value of threshold voltage | 1.14 | | (I > π x $I_{T(AV)}$), $T_J = T_J$ max. | |
| r_{t1} Low level value of on-state slope resistance | 1.18 | mΩ | (16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ max. | |
| r_{t2} High level value of on-state slope resistance | 1.14 | | (I > π x $I_{T(AV)}$), $T_J = T_J$ max. | |
| V_{TM} Max. on-state voltage | 1.96 | V | $I_{pk} = 750A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse | |
| I_H Maximum holding current | 600 | mA | $T_J = T_J$ max, anode supply 12V resistive load | |
| I_L Max. (typical) latching current | 1000 (300) | | | |

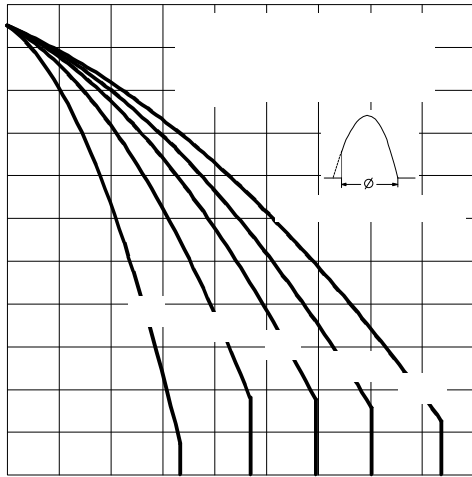


Fig. 3 - Current Ratings Characteristics

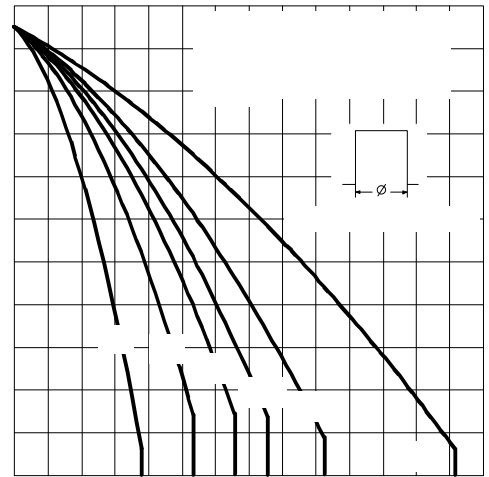


Fig. 4 - Current Ratings Characteristics

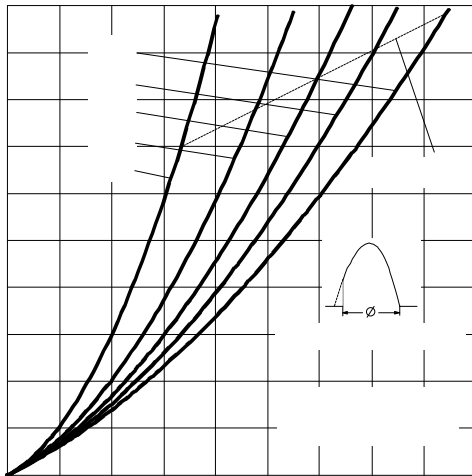


Fig. 5- On-state Power Loss Characteristics

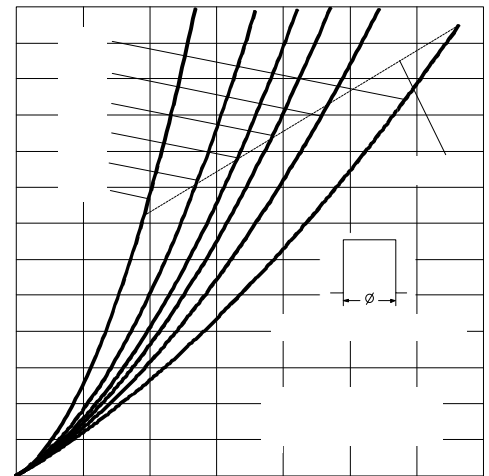


Fig. 6- On-state Power Loss Characteristics

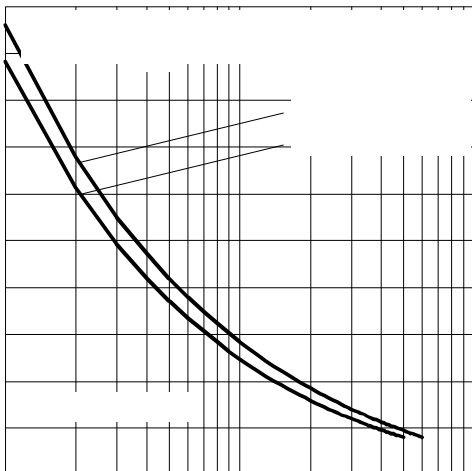


Fig. 7 - Maximum Non-Repetitive Surge Current

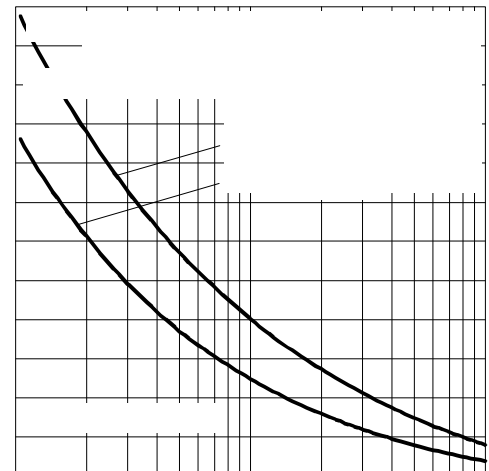


Fig. 8 - Maximum Non-Repetitive Surge Current

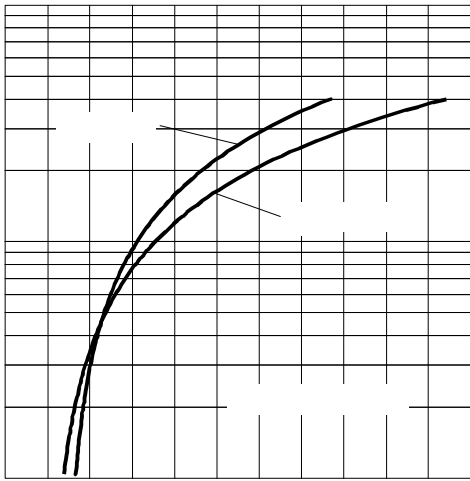


Fig. 9 - On-state Voltage Drop Characteristics

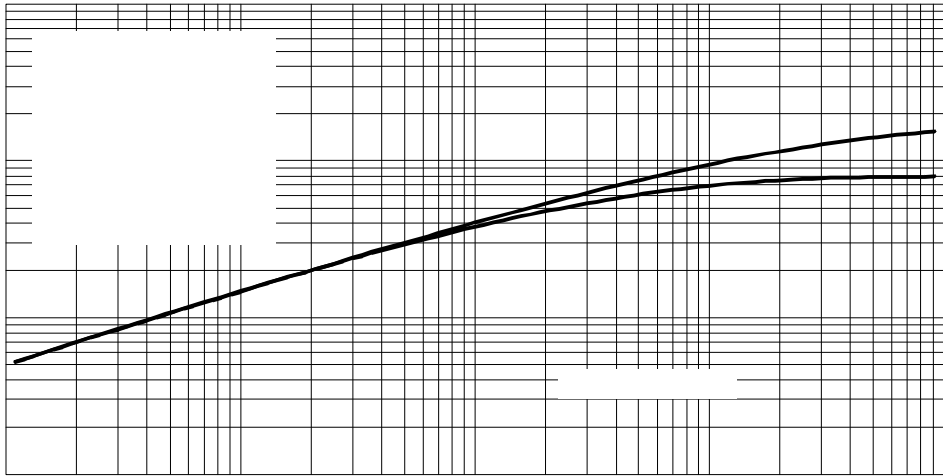


Fig. 10 - Thermal Impedance Z_{th-hs} Characteristics

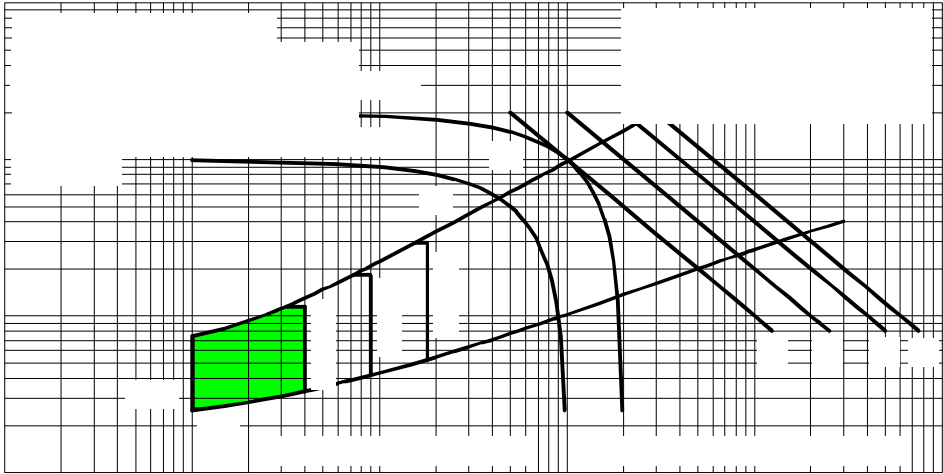


Fig. 11 - Gate Characteristics

Switching

| Parameter | ST180C..C | Units | Conditions |
|--|-----------|------------|---|
| di/dt Max. non-repetitive rate of rise of turned-on current | 1000 | A/ μ s | Gate drive 20V, 20 Ω , $t_r \leq 1\mu$ s $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$ |
| t_d Typical delay time | 1.0 | μ s | Gate current 1A, $di_g/dt = 1A/\mu$ s $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ\text{C}$ |
| t_q Typical turn-off time | 100 | | $I_{TM} = 300A$, $T_J = T_J$ max, $di/dt = 20A/\mu$ s, $V_R = 50V$ $dv/dt = 20V/\mu$ s, Gate 0V 100 Ω , $t_p = 500\mu$ s |

Blocking

| Parameter | ST180C..C | Units | Conditions |
|---|-----------|------------|--|
| dv/dt Maximum critical rate of rise of off-state voltage | 500 | V/ μ s | $T_J = T_J$ max linear to 80% rated V_{DRM} |
| I_{DRM} I_{RRM} Max. peak reverse and off-state leakage current | 30 | mA | $T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied |

Triggering

| Parameter | ST180C..C | | Units | Conditions | |
|---|-----------|------|---------------------------|--|---------------------------|
| P_{GM} Maximum peak gate power | 10 | | W | $T_J = T_J$ max, $t_p \leq 5$ ms | |
| $P_{G(AV)}$ Maximum average gate power | 2.0 | | | $T_J = T_J$ max, $f = 50\text{Hz}$, $d\% = 50$ | |
| I_{GM} Max. peak positive gate current | 3.0 | | A | $T_J = T_J$ max, $t_p \leq 5$ ms | |
| $+V_{GM}$ Maximum peak positive gate voltage | 20 | | V | $T_J = T_J$ max, $t_p \leq 5$ ms | |
| $-V_{GM}$ Maximum peak negative gate voltage | 5.0 | | | | |
| I_{GT} DC gate current required to trigger | TYP. | MAX. | mA | Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied | |
| | 180 | - | | | $T_J = -40^\circ\text{C}$ |
| | 90 | 150 | | | $T_J = 25^\circ\text{C}$ |
| V_{GT} DC gate voltage required to trigger | 40 | - | $T_J = 125^\circ\text{C}$ | | |
| | 2.9 | - | $T_J = -40^\circ\text{C}$ | | |
| | 1.8 | 3.0 | $T_J = 25^\circ\text{C}$ | | |
| I_{GD} DC gate current not to trigger | 10 | | mA | $T_J = T_J$ max | |
| | 0.25 | | | | V |
| V_{GD} DC gate voltage not to trigger | 0.25 | | V | Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied | |

Outline Table

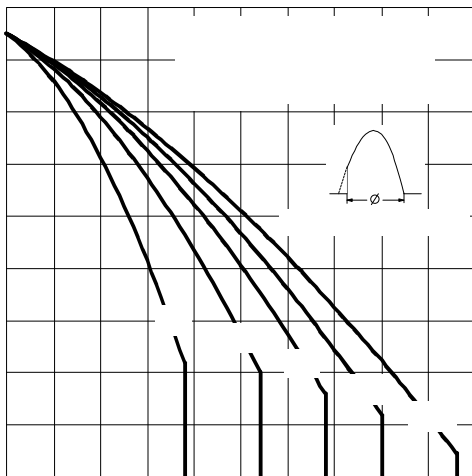
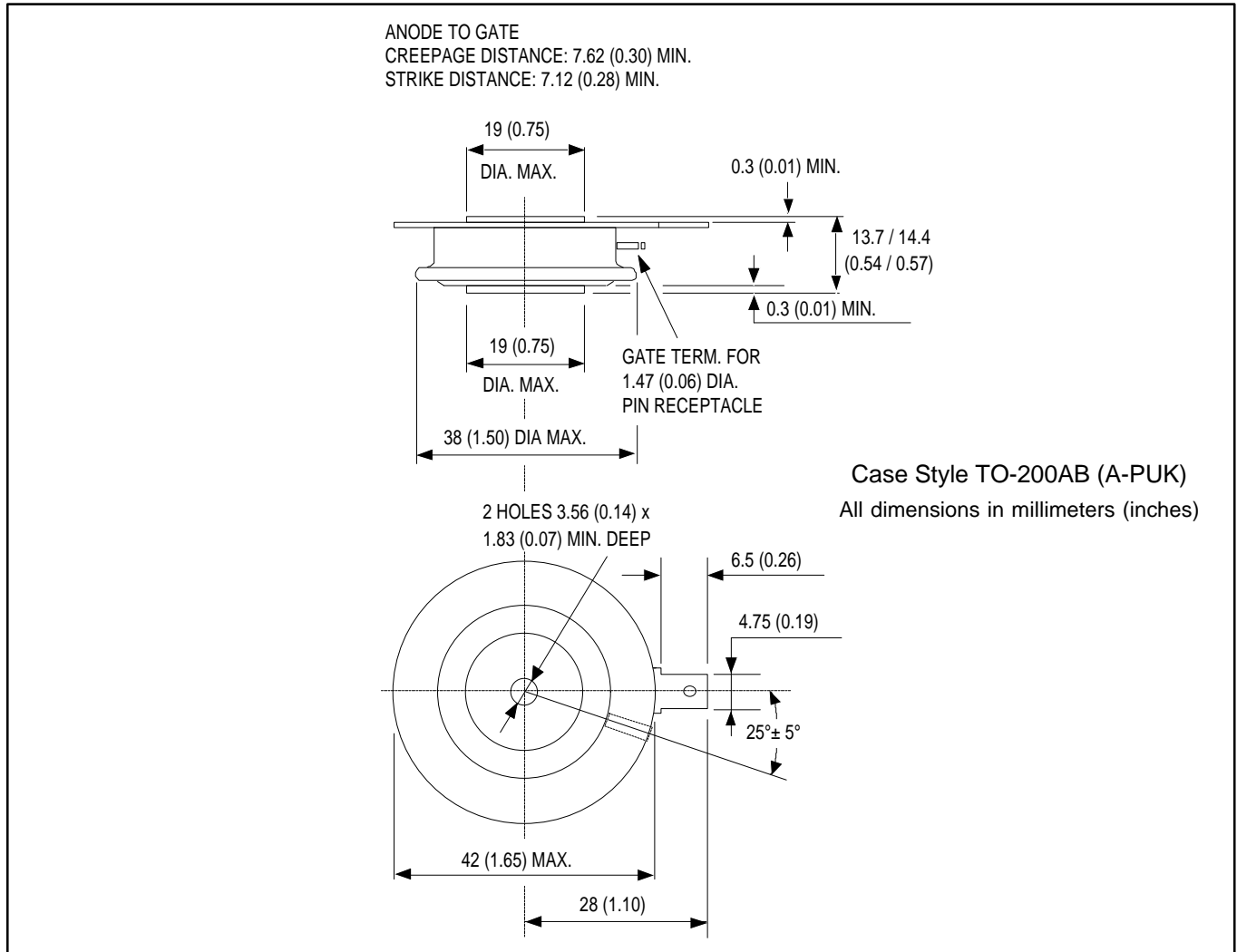


Fig. 1 - Current Ratings Characteristics

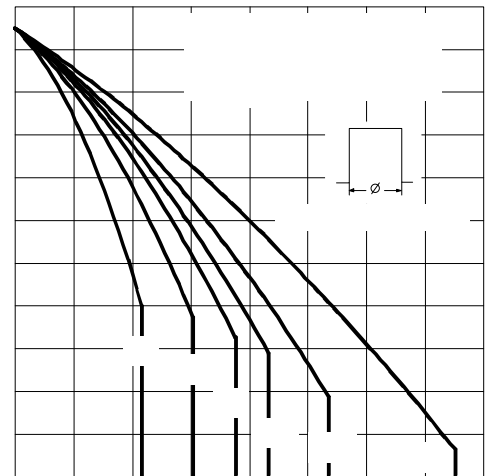


Fig. 2 - Current Ratings Characteristics